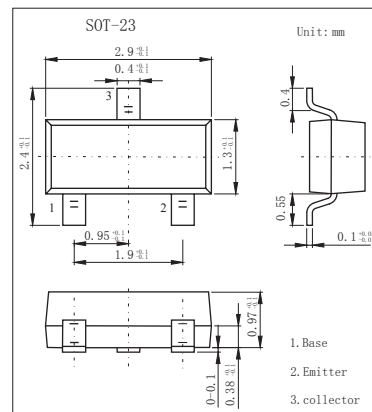


NPN Transistors

KST8050D

■ Features

- Collector Current: $I_C=1.5A$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	40	V
Collector-Emitter Voltage	V_{CE0}	25	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current -Continuous	I_C	1.5	A
Collector Dissipation	P_C	0.3	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_C = 100 \mu A, I_E = 0$	40			V
Collector-emitter breakdown voltage	V_{CE0}	$I_C = 1 mA, I_B = 0$	25			V
Emitter-base Breakdown voltage	V_{EB0}	$I_E = 100 \mu A, I_C = 0$	5			V
Collector-base cut-off current	I_{CB0}	$V_{CB} = 40 V, I_E = 0$			0.1	μA
Collector-emitter cut-off current	I_{CE0}	$V_{CE} = 20 V, I_B = 0$			0.1	μA
Emitter-base cut-off current	I_{EB0}	$V_{EB} = 5 V, I_C = 0$			0.1	μA
DC current gain	h_{FE}	$V_{CE} = 1 V, I_C = 100 mA$	120		400	
		$V_{CE} = 1 V, I_C = 800 mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 800 mA, I_B = 80 mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 800 mA, I_B = 80 mA$			1.2	V
Transition frequency	f_T	$V_{CE} = 10 V, I_C = 50 mA, f = 30 MHz$	100			MHz

■ h_{FE} Classification

Marking	Y1

KST8050D

Typical Characteristics

